

Product Features

- 50 860 MHz
- ±0.7 dB Gain Flatness
- +20 dBm P1dB
- +37 dBm Output IP3
- +73 dBm Output IP2 • -68 dBc CTB
- +34 dBmV/channel, 79 channels
- -80 dBc CSO +34 dBmV/channel, 79 channels
- Matched amplifiers for a push-pull configuration
- +7V Single Positive Supply
- MTTF > 1000 Years

Applications

- CATV Head End Equipment
- CATV Line Amplifiers
- FTTH Repeaters

Single-ended Device Specifications⁽¹⁾

Parameter	Units	Min	Тур	Max
Test Frequency	MHz		800	
Gain	dB	13.2	14.3	15.5
Output IP3 ⁽²⁾	dBm	+33.5	+36	
Device Current	mA	76	82.5	90
Device Voltage	V		5.25	

1. Test conditions unless otherwise noted: T = 25°C, 800 MHz on each individual single-branch amplifier in a 50Ω test fixture using a +7V supply and a 20.5 Ω dropping resistor.

2. 30IP measured with two tones at an output power of +5 dBm/tone separated by 1 MHz. The

Star mediate with two that and application power of admitted applicate of 21 rule.
 Typical parameters reflect performance in a push-pull application circuit.
 Balun, board, and connector losses have not been extracted, but typically account of 0.4 dB loss midband and 1.1 dB loss at 860 MHz.

5. Measured at +34 dBmV/channel, 79 channels Flat Loading.

6. OIP2 is measured at f1 + f2 at 5 dBm / tone.

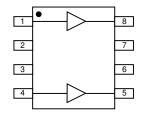
Product Description

The AG606 is a dual amplifier containing two internal matched amplifiers optimal for a push-pull configuration. The internal amplifiers employ InGaP HBT technology for a cost-effective low-distortion solution.

The AG606 is ideal for drop amplifiers, splitters, and other low to moderate power outside plant CATV applications. The amplifier can also be useful in low power headend applications such as linear laser drivers.

The AG606 has excellent VSWR when used in a 75 Ω push-pull configuration. It is provided in a low-cost environmentally-friendly lead-free/green/RoHS-compliant SOT-89 package.

Functional Diagram



Function	Pin No.
Amp 1 Input	1
Amp 2 Input	4
Amp 2 Output	5
Amp 1 Output	8
	2, 3, 6, 7,
Ground	Backside
	paddle

Typical Performance ⁽³⁾

Parameter	Units		Тур	ical		
Frequency	MHz	50	250	450	860	
Gain ⁽⁴⁾	dB	14.3	14.2	13.9	12.9	
Input Return Loss	dB	21	28	18	11	
Output Return Loss	dB	17	18	16	18	
CTB ⁽⁵⁾	dBc	-69	-67	-67		
CSO ⁽⁵⁾	dBc	-81	-87	-80		
XMOD ⁽⁵⁾	dBc	-60	-61	-60		
Output P1dB	dBm	+20.7	+20.5	+20.3	+22	
Output IP2 ⁽⁶⁾	dBm	+73.6	+76.1	+76.4	+76.6	
Output IP3 ⁽²⁾	dBm	+37.5	+37.5	+37.3	+39.2	
Noise Figure ⁽⁴⁾	dB	5	5	5.3	5.9	
Device Bias	V	+5.25 V @ 165 mA				

Absolute Maximum Rating

Parameter	Rating	Ordering l	Information
Operating Case Temperature	-40 to +85 °C	Part No.	Description
Storage Temperature	-55 to +125 °C	AG606*	Push-pull Dual Amplifier
Supply Voltage	+7 V	AG606-G	(lead-tin SOIC8 Pkg) Push-pull CATV Amplifier
RF Input Power (continuous)	+13dBm	A0000-0	(lead-free/green/RoHS-compliant SOIC8 Pkg)
Junction Temperature	+250 °C	AG606-PCB	Fully Assembled CATV Evaluation Board
		* This package is being	phased out in favor of the green package type which is backwards compatible for

existing designs.

Operation of this device above any of these parameters may cause permanent damage.

Specifications and information are subject to change without notice





Typical Device Data - **50** Ω **Z**₀

	These represent a s							kage.
Freq (MH	z) S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
50	-12.03	178.56	14.61	177.32	-18.85	-0.01	-17.45	178.57
100	-12.09	174.32	14.61	175.28	-18.74	-1.56	-17.08	178.23
150	-11.81	172.20	14.62	173.13	-18.76	-2.21	-17.28	176.63
200	-11.81	169.91	14.59	170.74	-18.81	-3.25	-16.86	176.45
250	-11.64	168.30	14.62	168.67	-18.77	-3.74	-17.24	173.88
300	-11.79	166.47	14.63	165.71	-18.81	-4.12	-17.00	174.14
350	-11.76	164.70	14.68	163.24	-18.79	-4.96	-17.20	172.40
400	-12.02	162.35	14.59	161.23	-18.84	-5.99	-16.85	173.24
450	-11.92	159.27	14.48	158.25	-18.82	-5.99	-17.02	170.87
500	-11.92	156.13	14.53	156.14	-18.80	-6.63	-16.70	169.98
550	-11.77	154.71	14.48	154.05	-18.86	-7.58	-16.78	167.35
600	-11.75	151.64	14.52	151.45	-18.79	-8.02	-16.47	167.79
650	-11.67	150.04	14.45	148.59	-18.74	-9.17	-16.49	164.94
700	-11.89	147.47	14.41	146.59	-18.83	-9.41	-16.48	164.76
750	-11.72	145.07	14.43	144.30	-18.89	-10.48	-16.43	161.86
800	-11.76	143.08	14.33	141.92	-18.87	-11.22	-16.23	161.91
850	-11.56	141.20	14.36	139.40	-18.87	-11.88	-15.86	158.92
900	-11.65	138.97	14.26	137.14	-18.80	-12.23	-15.78	159.88
950	-11.57	137.28	14.28	134.86	-18.79	-13.52	-15.51	156.89
1000	-11.56	135.12	14.19	132.17	-18.86	-13.15	-15.34	156.79

S-Parameters ($V_{dev} = +5.25$ V, $I_{cc} = 82.5$ mA, $T = 25^{\circ}$ C, unmatched 50 ohm system, calibrated to device leads) These represent a single-ended amplifier in the AG606, with there being two matched amplifiers inside the package

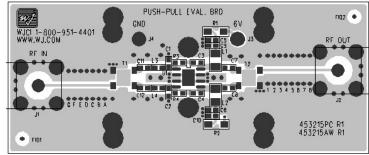
Typical Device Data – 37.5 Ω Z₀

S-Parameters (V_{dev} = +5.25 V, I_{cc} = 82.5 mA, T = 25°C, unmatched 37.5 ohm system, calibrated to device leads) These represent a single-ended amplifier in the AG606, with there being two matched amplifiers inside the package.

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Freq (MHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
50	-34.66	173.49	14.79	177.27	-18.66	-0.06	-19.98	-0.57
100	-33.64	133.95	14.81	175.12	-18.54	-1.71	-20.40	-3.63
150	-30.17	137.29	14.82	172.89	-18.56	-2.45	-20.15	-4.04
200	-29.21	131.02	14.80	170.45	-18.60	-3.54	-20.91	-7.28
250	-27.90	131.37	14.83	168.30	-18.57	-4.11	-20.34	-5.91
300	-28.12	124.34	14.84	165.33	-18.61	-4.51	-20.82	-9.61
350	-27.59	122.31	14.88	162.80	-18.59	-5.40	-20.57	-10.25
400	-27.52	110.86	14.79	160.77	-18.65	-6.45	-21.33	-14.80
450	-25.69	107.75	14.68	157.66	-18.62	-6.58	-21.31	-13.74
500	-24.49	101.63	14.73	155.45	-18.61	-7.32	-21.94	-15.66
550	-23.76	104.95	14.68	153.27	-18.66	-8.35	-22.13	-13.89
600	-22.84	100.16	14.72	150.61	-18.59	-8.86	-22.79	-18.83
650	-22.46	101.72	14.65	147.66	-18.53	-10.10	-23.13	-17.61
700	-22.06	95.00	14.60	145.62	-18.64	-10.38	-23.54	-19.44
750	-21.15	95.84	14.62	143.20	-18.70	-11.58	-24.06	-16.74
800	-20.79	94.07	14.53	140.77	-18.68	-12.37	-25.05	-20.60
850	-20.09	95.55	14.56	138.11	-18.67	-13.17	-26.61	-16.06
900	-19.78	92.24	14.45	135.83	-18.60	-13.53	-27.43	-23.50
950	-19.42	92.70	14.48	133.44	-18.59	-14.94	-29.28	-17.34
1000	-18.88	90.91	14.39	130.68	-18.66	-14.64	-31.32	-18.82



Application Circuit PC Board Layout



Circuit Board Material: .028" FR4, 4 - layer, 1 oz copper, Microstrip line details: width = .021", spacing = .021". C1, C2, R3, C3, R4 and C4 are shown in the silkscreen but are not required in the schematic.

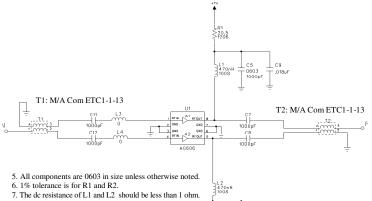
Typical RF Performance at 25°C

Frequency	MHz	50	250	450	860	
Gain ⁽¹⁾	dB	14.3	14.2	13.9	12.9	
Input R.L.	dB	21	28	18	11	
Output R.L.	dB	17	18	16	18	
CTB ⁽²⁾	dBc	-69	-67	-67		
CSO ⁽²⁾	dBc	-81	-87	-80		
XMOD ⁽²⁾	dBc	-60	-61	-60		
Output P1dB	dBm	+20.7	+20.5	+20.3	+22	
Output IP2 ⁽³⁾	dBm	+73.6	+76.1	+76.4	+76.6	
Output IP3 ⁽⁴⁾	dBm	+37.5	+37.5	+37.3	+39.2	
Noise Figure ⁽¹⁾	dB	5	5	5.3	5.9	
Device Current	mA	165				
Device Voltage	V	V +5.25				
1. Balun, board, and connector losses have not been extracted, but typically account for						

CSO, CTB, & XMOD are measured at +34 dBmV/channel, 79 channels Flat Loading.
 OIP2 is measured at f1 + f2 at 5 dBm / tone.

0.4 dB loss midband and 1.1 dB loss at 860 MHz.

4. OIP3 is measured at 5 dBm / tone with 1 MHz spacing.



5.9 7. The defesistance of E1 and E2 should be

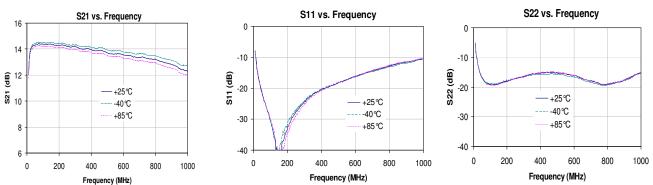


Recommended Bias Resistor Values

Supply Voltage	R1/R2 Value	Size
7 V	20.5 ohms	1206
8 V	32.5 ohms	1210
9 V	44.5 ohms	2010
10 V	56.5 ohms	2010
12 V	81 ohms	2010
24 V	227 ohms	2 Watts

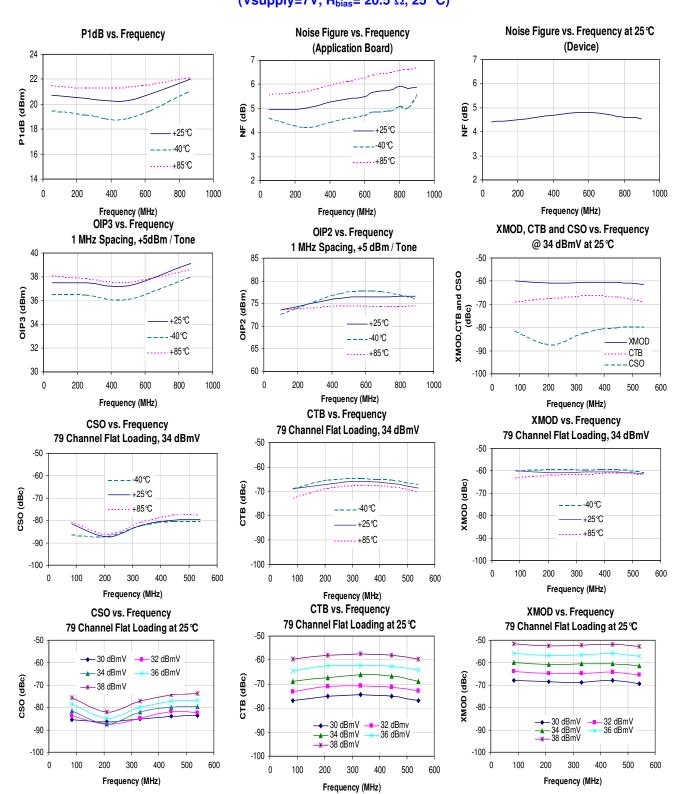
75 Ω **Push-Pull Application Circuit Performance**

(Vsupply = +7 V, R_{bias} = 20.5 Ω , 25° C)



Specifications and information are subject to change without notice.

75 Ω Push-Pull Application Circuit Performance (Cont'd) (Vsupply=7V, R_{bias}= 20.5 Ω, 25° C)



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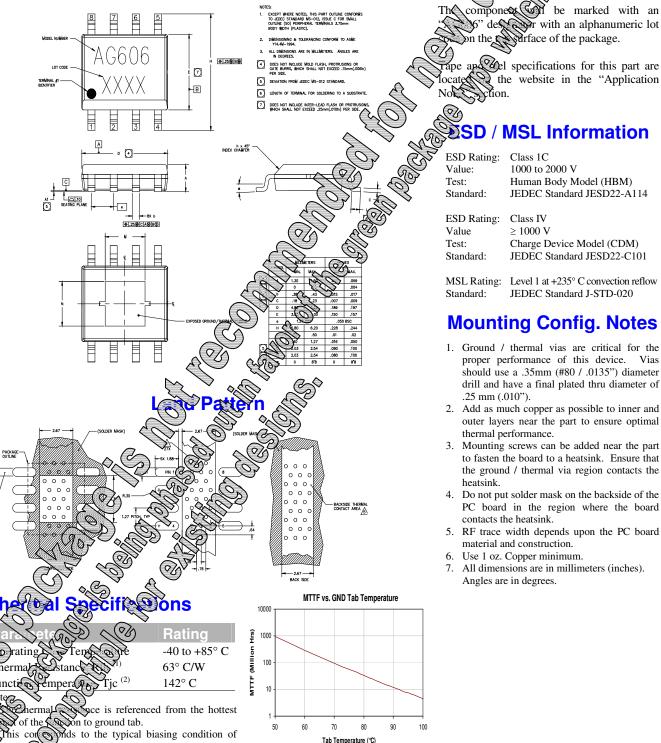
Car Information

Marking

AG606 (SOIC-8 Package) Mechanical Information

This package may contain lead-bearing materials. The plating material on the lead de state.

Outline Drawing

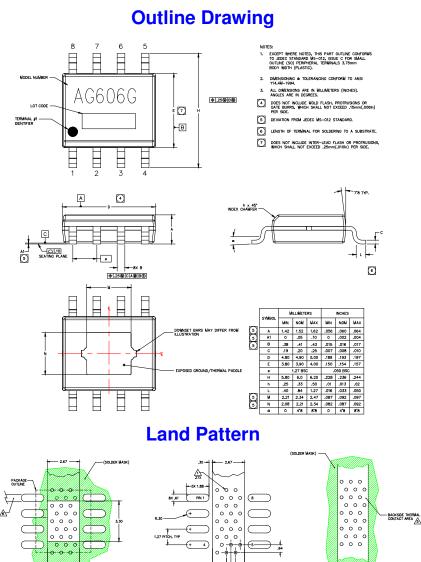


+5.16 Chos mA at an 85° C case temperature. A minimum MTTF of 1 million hours is achieved for junction temperatures below 177° C.



AG606-G (Lead-Free Package) Mechanical Information

This package is lead-free/green/RoHS-compliant. The plating material on the leads is NiPdAu. It is compatible with both lead-free (maximum 260°C reflow temperature) and lead (maximum 245°C reflow temperature) soldering processes.



Product Marking

The component will be marked with an "AG606G" designator with an alphanumeric lot code on the top surface of the package.

Tape and reel specifications for this part are located on the website in the "Application Notes" section.

ESD / MSL Information

ESD Rating:	Class 1C
Value:	1000 to 2000 V
Test:	Human Body Model (HBM)
Standard:	JEDEC Standard JESD22-A114
ESD Rating:	Class IV
Value	Passes greater than 1000 V
Test:	Charge Device Model (CDM)
Standard:	JEDEC Standard JESD22-C101
MSL Rating:	Level 2 at +260° C convection reflow

Mounting Config. Notes

Standard:

JEDEC Standard J-STD-020A

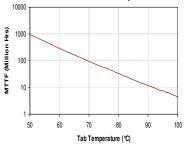
- Ground / thermal vias are critical for the proper performance of this device. Vias should use a .35mm (#80/.0135") diameter drill and have a final plated through diameter of .25mm (.010")
- 2. Add as much copper as possible to inner and outer layers
- To ensure reliable operation, device ground paddle-toground pad solder joint is critical.
- Add mounting screws near the part to fasten the board to a heatsink. Ensure that the ground / thermal via region contract the heatsing.
- contacts the heatsink. 5. For optimal thermal performance, expose soldermask
 - For optimal thermal performance, expose soldermask on backside where it contacts the heatsink.
 RF trace width depends upon the PC board material and
 - KF trace width depends upon the PC board material an construction.
 Use 1 oz. Copper minimum.
- 5. Ose to in copper infinition.
 5. If the PCB design rules allow, ground vias should be placed under the land pattern for better RF and thermal performance. Otherwise ground vias should be placed as close to the land pattern as possible.
- All dimensions are in mm. Angles are in degrees.

Thermal Specifications

Parameter	Rating
Operating Case Temperature	-40 to +85° C
Thermal Resistance, Rth ⁽¹⁾	63° C/W
Junction Temperature, Tjc ⁽²⁾	142° C

Notes:

- 1. The thermal resistance is referenced from the hottest part of the junction to ground tab underneath the device.
- This corresponds to the typical biasing condition of +5.16V, 175 mA at an 85° C case temperature. A minimum MTTF of 1 million hours is achieved for junction temperatures below 177° C.



MTTF vs. GND Tab Temperature